onsemi

NPN Darlington Transistor

NZT7053

This device is designed for applications requiring extremely high gain at collector currents to 1.0 A and high breakdown voltage. Sourced from Process 06.

ABSOLUTE MAXIMUM RATINGS (Notes 1, 2)

$(T_A = 25^{\circ}C \text{ unless otherwise noted.})$	
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Symbol	Parameter	Value	Unit
V _{CEO}	Collector-Emitter Voltage	100	V
V _{CBO}	Collector-Base Voltage	100	V
V _{EBO}	Emitter-Base Voltage	12	V
Ι _C	Collector Current – Continuous	1.5	А
T _J , T _{STG}	Operating and Storage Junction Temperature Range	–55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. These ratings are based on a maximum junction temperature of 150°C.

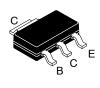
2. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

THERMAL CHARACTERISTICS (Note 3)

 $(T_A = 25^{\circ}C \text{ unless otherwise noted.})$

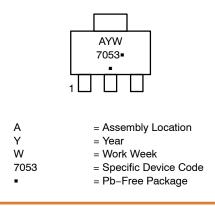
Symbol	Characteristics	Value	Unit
PD	Total Device Dissipation	1000	mW
	Derate Above 25°C	8.0	mW/°C
R_{\thetaJA}	Thermal Resistance, Junction to Ambient	125	°C/W

3. Device mounted on FR–4 PCB 36 mm \times 18 mm \times 1.5 mm; mounting pad for the collector lead min. 6 cm².



SOT-223 CASE 318H

MARKING DIAGRAM



ORDERING INFORMATION

Device	Package	ackage Shipping [†]	
NZT7053	SOT-223	4000 /	
	(Pb-Free)	Tape & Reel	

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, <u>BRD8011/D</u>.

NZT7053

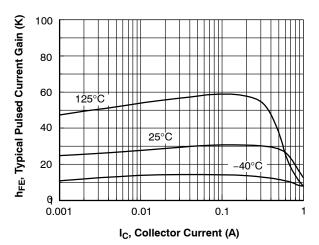
ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted.)

Symbol	Parameter	Conditions	Min.	Max.	Unit
OFF CHARAC	TERISTICS			•	-
V _{(BR}) _{CEO}	Collector-Emitter Breakdown Voltage (Note 4)	I _C = 1.0 mA, I _B = 0	100	-	V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = 100 μA, I _E = 0	100	-	V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 1.0 mA, I _C = 0	12	-	V
I _{CBO}	Collector-Cutoff Current	$V_{CB} = 80 \text{ V}, I_E = 0$	-	0.1	μA
I _{CES}	Emitter-Cutoff Current	$V_{CE} = 80 \text{ V}, I_E = 0$	-	0.2	μA
I _{EBO}	Emitter-Cutoff Current	V _{EB} = 7.0 V, I _C = 0	-	0.1	μA
ON CHARACT	TERISTICS (Note 4)				
h _{FE}	DC Current Gain	I_{C} = 100 mA, V_{CE} = 5.0 V	10000	-	
		I _C = 1.0 A, V _{CE} = 5.0 V	1000	20000	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 100 mA, I _B = 0.1 mA	-	1.5	V
V _{BE(on)}	Base-Emitter On Voltage	I_{C} = 100 mA, V_{BE} = 5.0 V	-	2.0	V
SMALL SIGN	AL CHARACTERISTICS				
F _T	Transition Frequency	I_{C} = 100 mA, V_{CE} = 5.0 V	200	-	MHz

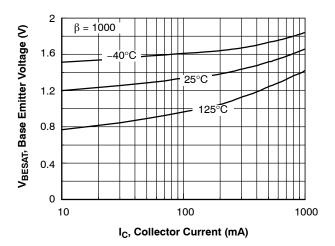
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 4. Pulse test: pulse width \leq 300 µs, duty cycle \leq 2%

NZT7053

TYPICAL CHARACTERISTICS









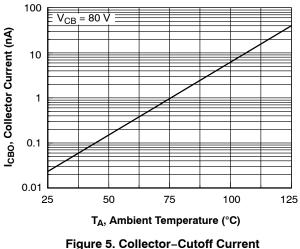


Figure 5. Collector–Cutoff Current vs. Ambient Temperature

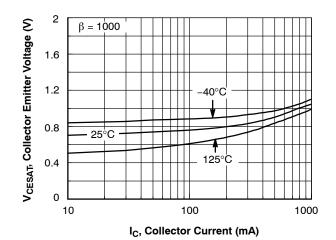
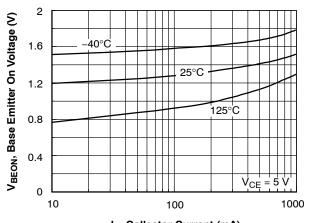
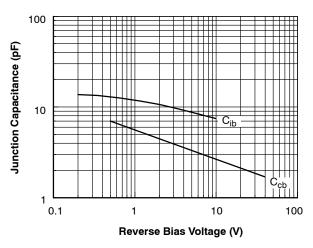


Figure 2. Collector–Emitter Saturation Voltage vs. Collector Current



I_C, Collector Current (mA)

Figure 4. Base Emitter ON Voltage vs. Collector Current





NZT7053

TYPICAL CHARACTERISTICS (continued)

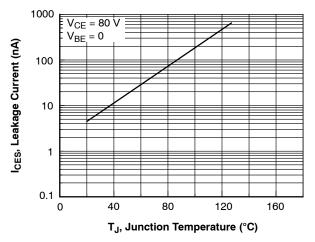


Figure 7. Typical Collector–Emitter Leakage Current vs. Temperature

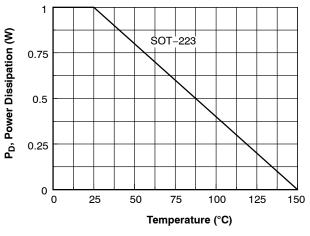


Figure 8. Power Dissipation vs. Ambient Temperature

SOT-223 CASE 318H ISSUE B DATE 13 MAY 2020 A NDTES SCALE 2:1 DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009. CONTROLLING DIMENSION: MILLIMETERS DIMENSIONS D & E1 ARE DETERMINED AT DATUM H. DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSIONS DG GATE BURRS. SHALL NOT EXCEED 0.23mm PER SIDE. LEAD DIMENSIONS & AND &1 DO NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBBAR PROTRUSION IS 0.08mm PER SIDE. DATUMS A AND B ARE DETERMINED AT DATUM H. A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY. POSITIONAL TOLERANCE APPLIES TO DIMENSIONS & AND &1. DIMENSIONING AND TOLERANCING PER ASME 1. b1 2 з. В 4. 5. 6. 7. b AND b1. MILLIMETERS DIM MIN. NITM. MAX. e ___ ___ 1.80 k Α \oplus 0.10 \otimes C A B 0.02 0.06 0.11 A1 TOP VIEW NDTE 7 0.60 0.74 0.88 b 2.90 3.10 b1 3.00 DETAIL A 0.24 ____ 0.35 С H 6.70 D 6.30 6.50 Ε 6.70 7.00 7.30 E1 3.30 3.50 3.70 0.10 C 2.30 BSC e SIDE VIEW FND VIEW L 0.25 ___ i 10° 0° ____ -3.80 2.00 Α1 DETAIL A 8.30 3x= Assembly Location GENERIC A 2.00 **MARKING DIAGRAM*** Y = Year = Work Week w XXXXX = Specific Device Code = Pb-Free Package 5'30 AYW 3x 1.50 (Note: Microdot may be in either location) XXXXX= PITCH *This information is generic. Please refer to RECOMMENDED MOUNTING FOOTPRINT device data sheet for actual part marking. For additional information on our Pb-Free strategy Pb-Free indicator, "G" or microdot "•", may ж and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D. or may not be present. Some products may not follow the Generic Marking. Electronic versions are uncontrolled except when accessed directly from the Document Repository. **DOCUMENT NUMBER:** 98ASH70634A Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. **DESCRIPTION:** SOT-223 PAGE 1 OF 1

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